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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/499,027	02/07/2000	Masahiro Hosoda	900-318	9626
75	90 09/25/2002			
NIXON & VANDERHYE P.C. 1100 North Glebe Road 8th Floor			EXAMINER	
			FLORES RUIZ, DELMA R	
Arlington, VA	22201-4/14		ART UNIT	PAPER NUMBER
			2828	
			DATE MAILED: 09/25/2002	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Application No.	Applicant(s)			
• •		09/499,027	HOSODA ET AL.			
مه	Office Action Summary	Examiner	Art Unit			
		Delma R. Flores Ruiz	2828			
Period fo	The MAILING DATE of this communication app or Reply	ears on the cover sheet w	ith the correspondence address			
THE I - Exter after - If the - If NO - Failu - Any I	ORTENED STATUTORY PERIOD FOR REPLY MAILING DATE OF THIS COMMUNICATION. Inscions of time may be available under the provisions of 37 CFR 1.13 SIX (6) MONTHS from the mailing date of this communication. Period for reply specified above is less than thirty (30) days, a reply period for reply is specified above, the maximum statutory period or reply within the set or extended period for reply will, by statute, eply received by the Office later than three months after the mailing and patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a of this within the statutory minimum of this will apply and will expire SIX (6) MON, cause the application to become Al	reply be timely filed ty (30) days will be considered timely. ITHS from the mailing date of this communication. BANDONED (35 U.S.C. § 133).			
1)⊠	Responsive to communication(s) filed on <u>06/2</u>	<u>26/2002</u> .				
2a) <u></u> ☐	This action is FINAL . 2b)⊠ Th	is action is non-final.				
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under Ex parte Quayle, 1935 C.D. 11, 453 O.G. 213. Disposition of Claims						
4)	Claim(s) is/are pending in the application	on.				
	4a) Of the above claim(s) is/are withdraw	wn from consideration.				
5)	Claim(s) is/are allowed.		Parel D			
6)⊠	Claim(s) 1-11,16 and 17 is/are rejected.		PAUL IP			
7)	Claim(s) is/are objected to.		SUPERVISORY PATENT EXAMINER			
•	Claim(s) are subject to restriction and/o	r election requirement.	TECHNOLOGY CENTER 2800			
Applicati	on Papers					
9) The specification is objected to by the Examiner.						
10) The drawing(s) filed on is/are: a) □ accepted or b) □ objected to by the Examiner.						
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).						
11)	The proposed drawing correction filed on		isapproved by the Examiner.			
If approved, corrected drawings are required in reply to this Office action.						
<i>,</i> —	The oath or declaration is objected to by the Ex	animer.				
-	inder 35 U.S.C. §§ 119 and 120		2.440(.) (4) (0			
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).						
a)[☐ All b)☐ Some * c)☐ None of:	- b b				
1. Certified copies of the priority documents have been received.						
2. Certified copies of the priority documents have been received in Application No						
 3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)). * See the attached detailed Office action for a list of the certified copies not received. 						
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).						
a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachmen	t(s)					
2) Notic	e of References Cited (PTO-892) e of Draftsperson's Patent Drawing Review (PTO-948) nation Disclosure Statement(s) (PTO-1449) Paper No(s) _	5) Notice of	Summary (PTO-413) Paper No(s) Informal Patent Application (PTO-152)			
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DETAILED ACTION

Claim Rejections - 35 USC § 102

The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

Claims 1 – 10 and 16 – 1 7, are rejected under 35 U.S.C. 102(e) as being anticipated by Tanaka et al (5,974,069).

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Regarding claims 1 – 10, and 16 – 17, Tanaka discloses a semiconductor laser device comprising; a plurality of semiconductor laser resonators having light emitting layers of materials different (Column 5, lines 26 – 35) from each other, the semiconductor laser resonators being provided on the same semiconductor substrate so that the light emitting layers lie substantially in parallel to a main surface of the semiconductor substrate, and a high-resistance region provided between the semiconductor laser resonators (Figs 1 – 2, 4, 8a-c, 9, 11 – 14, and 16 – 19, Column 3, lines 13 – 16). The semiconductor laser device, wherein the semiconductor substrate is GaAs substrate (Abstract, Column 25, lines 22 - 27) and the light emitting layers of the semiconductor laser resonators contain Group V element different from each other and the Group V elements are selected from the group consisting of P, As, Sb and N (Column 1, lines 13 – 20, Column 7, lines 32 – 42) The semiconductor laser resonators comprises two resonators having oscillation wavelength in a red region and infrared region, respectively (Column 2, lines 61 – 65). The semiconductor substrate is a GaAs substrate, and the resonator having an oscillation wavelength in a red region includes a light emitting layer formed of an InGaP based material and the resonator having an oscillation wavelength in an infrared region includes a light emitting layer formed of a GaAs based material (Column 1, lines 13 – 20, Column 7, lines 32 – 42, Column 16, lines 40 – 67, Column 24, lines 24 – 31). The light emitting layers of the semiconductor laser resonators lie at substantially the same distance from the main surface of the semiconductor substrate (Figs 1-2, 4, 8a-c, 9, 11-14, and 16-19). The

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semiconductor laser resonators each have a refractive index wave-guiding structure and the high resistance regions is formed as a sufficient air gap and high resistively semiconductor layer having a sufficient resistance for electrically isolating adjacent semiconductor laser resonator (Column 2, lines 61 - 65, Column 4, lines 54 - 60, Column 8, lines 66 - 67, Column 9, lines 1 - 16 and Column 16, lines 40 - 67). The high-resistivity semiconductor laser is formed by implanting protons or gallium ions (Column 3, lines 13 - 16).

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 11 is rejected under 35 U.S.C. 103(a) as being unpatentable over Motoda et al (5,872,002) in view of Doi et al (5,793,790).

It would have been obvious at the time of applicant's invention, to combine Doi of teaching an incorporated in a recording and reproducing apparatus capable of performing recording and reproducing for both CD and DVD with semiconductor laser device because the CD and DVD use to reproducing and date reading operation. The

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semiconductor laser device is usually incorporated for use in an optical pick up in a recording and reproducing apparatus capable of performing the recording and reproducing operation.

Response to Arguments

Applicant's arguments with respect to claims 1-11, and 16-17 have been considered but are most in view of the new ground(s) of rejection.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Delma R. Flores Ruiz whose telephone number is (703) 308-6238. The examiner can normally be reached on M - F.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Paul Ip can be reached on (703) 308-3098. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 308-7722 for regular communications and (703) 308-7724 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 306-3431.

Delma R. Flores Ru

Examiner Art Unit 2828

Paul Ip Supervisor Patent Examiner Art Unit 2828

Drfr September 9, 2

September 9, 2002